

Harald Schneider

List of Publications by Year in descending order

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330
papers

6,295
citations

94433

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67
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all docs

337
docs citations

337
times ranked

4873
citing authors

#	ARTICLE	IF	CITATIONS
1	Pump-induced terahertz anisotropy in bilayer graphene. <i>Physical Review B</i> , 2022, 105, .	3.2	2
2	Terahertz control of photoluminescence emission in few-layer InSe. <i>Applied Physics Letters</i> , 2022, 120, .	3.3	4
3	Ultrafast phenomena and terahertz waves: introduction. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2022, 39, UPT1.	2.1	3
4	Preventing the breakdown of photoconductive terahertz emitter at high bias-field operation. , 2021, , .		0
5	High-field charge transport in InGaAs nanowires. , 2021, , .		0
6	Limitation of THz conversion efficiency in DSTMS pumped by intense femtosecond pulses. <i>Optics Express</i> , 2021, 29, 22494-22503.	3.4	2
7	High-Field Operation of GaAs Photoconductive Terahertz Emitters. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2021, 42, 537-546.	2.2	4
8	A Two-Dimensional Polyimide-Graphene Heterostructure with Ultrafast Interlayer Charge Transfer. <i>Angewandte Chemie - International Edition</i> , 2021, 60, 13859-13864.	13.8	18
9	Investigation of an Opposed-Contact GaAs Photoconductive Semiconductor Switch at 1-kHz Excitation. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 2355-2359.	3.0	14
10	High-field THz pulses from a GaAs photoconductive emitter for non-linear THz studies. <i>Optics Express</i> , 2021, 29, 19920.	3.4	4
11	Anisotropic Terahertz Pump-Probe Response of Bilayer Graphene. , 2021, , .		0
12	Actively mode-locked pulses from a mid-IR quantum cascade laser. , 2021, , .		0
13	Enhanced Trion Emission in Monolayer MoSe ₂ by Constructing a Type-I Van Der Waals Heterostructure. <i>Advanced Functional Materials</i> , 2021, 31, 2104960.	14.9	21
14	Optical Kerr nonlinearity and multiphoton absorption of DSTMS measured by the Z-scan method. <i>Journal of the Optical Society of America B: Optical Physics</i> , 2021, 38, 2511.	2.1	1
15	Kinetic Monte Carlo Simulation of Exciton Hopping: Urbach Tails in Gas-Molecule Decorated MoSe ₂ . <i>Physica Status Solidi (B): Basic Research</i> , 2021, 258, 2100186.	1.5	0
16	Gold implanted germanium photoswitch for cavity dumping of a free-electron laser. <i>Applied Physics Letters</i> , 2021, 118, .	3.3	4
17	BaFe ₂ As ₂ Investigated by Pump-Probe Spectroscopy under High Pressures. , 2021, , .		0
18	Silicon-Based Intermediate-Band Infrared Photodetector Realized by Te Hyperdoping. <i>Advanced Optical Materials</i> , 2021, 9, 2001546.	7.3	19

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19	Improved Germanium photoswitch for cavity dumping of a free-electron laser. , 2021, , .		0
20	THz conversion efficiency in DSTMS limited by high-order nonlinearities. , 2021, , .		0
21	Fifth-harmonic generation in Si:B pumped with intense terahertz pulses. , 2021, , .		0
22	Terahertz modulation of the trion resonance in MoSe2 monolayer. , 2021, , .		0
23	High electron mobility in strained GaAs nanowires. Nature Communications, 2021, 12, 6642.	12.8	28
24	Mode-locked short pulses from an 8 μ m wavelength semiconductor laser. Nature Communications, 2020, 11, 5788.	12.8	37
25	Performance Investigation of Bulk Photoconductive Semiconductor Switch Based on Reversely Biased p-n Structure. IEEE Transactions on Electron Devices, 2020, 67, 4963-4969.	3.0	5
26	Intracavity third-harmonic generation in Si:B pumped by intense terahertz pulses. Physical Review B, 2020, 102, .	3.2	21
27	Nonlinear Charge Transport in InGaAs Nanowires at Terahertz Frequencies. Nano Letters, 2020, 20, 3225-3231.	9.1	12
28	Up to 70 THz bandwidth from an implanted Ge photoconductive antenna excited by a femtosecond Er:fibre laser. Light: Science and Applications, 2020, 9, 30.	16.6	37
29	Broadband Photodetectors: Demonstration of a Broadband Photodetector Based on a Two-Dimensional Metal-Organic Framework (Adv. Mater. 9/2020). Advanced Materials, 2020, 32, 2070071.	21.0	2
30	Demonstration of a Broadband Photodetector Based on a Two-Dimensional Metal-Organic Framework. Advanced Materials, 2020, 32, e1907063.	21.0	103
31	Photoluminescence dynamics in few-layer InSe. Physical Review Materials, 2020, 4, .	2.4	14
32	All-THz pump-probe spectroscopy of the intersubband AC-Stark effect in a wide GaAs quantum well. Optics Express, 2020, 28, 25358.	3.4	2
33	Ultrashort pulses from a 8 μ m wavelength semiconductor laser. , 2020, , .		0
34	Nonlinear plasmonic response in GaAs/InGaAs core/shell nanowires. , 2020, , .		0
35	Non-plasmonic improvement in photoconductive THz emitters using nano- and micro-structured electrodes. Optics Express, 2020, 28, 35490.	3.4	3
36	Nonlinear IR and THz Spectroscopy of Semiconductor Nanowires. , 2020, , .		0

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37	Effective Hexagonal Boron Nitride Passivation of Few-Layered InSe and GaSe to Enhance Their Electronic and Optical Properties. ACS Applied Materials & Interfaces, 2019, 11, 43480-43487.	8.0	44
38	Pump-probe THz spectroscopy study of electronic properties of semiconductor nanowires. , 2019, , .		1
39	Transient Characteristics of Interdigitated GaAs Photoconductive Semiconductor Switch at 1-kHz Excitation. IEEE Electron Device Letters, 2019, 40, 1136-1138.	3.9	8
40	Broadband and High Electric Field THz Pulse Emission from Photoconductive Emitters. , 2019, , .		0
41	Widely tunable GaAs bandgap via strain engineering in core/shell nanowires with large lattice mismatch. Nature Communications, 2019, 10, 2793.	12.8	78
42	Absorption edge, urbach tail, and electron-phonon interactions in topological insulator Bi ₂ Se ₃ and band insulator (Bi _{0.89} In _{0.11}) ₂ Se ₃ . Applied Physics Letters, 2019, 114, .	3.3	10
43	Optical pump-probe THz probe response of VO ₂ under high pressure. EPJ Web of Conferences, 2019, 205, 04003.	0.3	0
44	Exciton localization in MoSe ₂ monolayers induced by adsorbed gas molecules. Applied Physics Letters, 2019, 114, 172106.	3.3	15
45	Plasmonic field guided patterning of ordered colloidal nanostructures. Nanophotonics, 2019, 8, 505-512.	6.0	5
46	Electron dynamics in In _x Ga _{1-x} As shells around GaAs nanowires probed by terahertz spectroscopy. Nanotechnology, 2019, 30, 244004.	2.6	9
47	Effect of the dopant location and the number of Bragg mirrors on the performance of superlattice infrared photodetectors. , 2019, , .		0
48	Scalable Large-Area Terahertz Emitters with Improved Electrode Design. , 2019, , .		1
49	Ultrafast metallization in NbO ₂ studied by pump-probe THz spectroscopy. , 2019, , .		0
50	Plasmonic nonlinearity in GaAs/In _{0.20} Ga _{0.80} As core/shell nanowires. , 2019, , .		0
51	Cavity enhanced third-harmonic generation in Si:B pumped with intense terahertz pulses. , 2019, , .		0
52	Nonthermal nature of photoinduced insulator-to-metal transition in NbO_2 . Physical Review B, 2019, 99, .	3.2	15
53	Nonlinear plasmonic response of doped nanowires observed by infrared nanospectroscopy. Nanotechnology, 2019, 30, 084003.	2.6	10
54	Improved electrode design for interdigitated large-area photoconductive terahertz emitters. Optics Express, 2019, 27, 13108.	3.4	17

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55	Filling the 5-10 THz gap using Ge-based photoconductive emitter. , 2019, , .		0
56	Infrared nanoscopy down to liquid helium temperatures. Review of Scientific Instruments, 2018, 89, 033702.	1.3	16
57	Dressing Intersubband Transitions at Terahertz Frequencies. , 2018, , .		0
58	FELBE -Upgrades and Status of the IRITHz FEL User Facility at HZDR. , 2018, , .		5
59	Broadband Spectrum from a Photoconductive Emitter Spanning up to 13 THz. , 2018, , .		0
60	Theoretical analysis of the length distributions of Ga-catalyzed GaAs nanowires. Journal of Physics: Conference Series, 2018, 1124, 022039.	0.4	0
61	Enhanced photoresponses of an optically driven VO ₂ -based terahertz wave modulator near percolation threshold. Applied Physics Letters, 2018, 113, .	3.3	10
62	A simple route to synchronized nucleation of self-catalyzed GaAs nanowires on silicon for sub-Poissonian length distributions. Nanotechnology, 2018, 29, 504004.	2.6	15
63	Ultrafast response of photoexcited carriers in VO ₂ at high-pressure. New Journal of Physics, 2018, 20, 083003.	2.9	15
64	Fano signatures between intersubband and ponderomotive responses in MQW structures. Optics Express, 2018, 26, 24054.	3.4	0
65	Extended Infrared Photoresponse in Te -Hyperdoped Si at Room Temperature. Physical Review Applied, 2018, 10, .	3.8	45
66	Gapless Broadband Terahertz Emission from a Germanium Photoconductive Emitter. ACS Photonics, 2018, 5, 2718-2723.	6.6	30
67	Low-energy carrier dynamics in graphene and other 2D materials. , 2018, , .		0
68	Giant impact of self-photothermal on light-induced ultrafast insulator-to-metal transition in VO ₂ nanofilms at terahertz frequency. Optics Express, 2018, 26, 28051.	3.4	12
69	Nonlinear Plasmonic Response of Doped GaAs Nanowires Observed in s-SNIM. , 2018, , .		0
70	Dynamics of non-equilibrium charge carriers in p-germanium doped by gallium. Physica Status Solidi (B): Basic Research, 2017, 254, 1600803.	1.5	8
71	Four-Wave Mixing in Landau-Quantized Graphene. Nano Letters, 2017, 17, 2184-2188.	9.1	25
72	Quantum Interference Current in InSb Injected by Intense Terahertz Radiation. Journal of Infrared, Millimeter, and Terahertz Waves, 2017, 38, 808-812.	2.2	1

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73	Room-temperature short-wavelength infrared Si photodetector. <i>Scientific Reports</i> , 2017, 7, 43688.	3.3	79
74	Doubly Dressed Bosons: Exciton Polaritons in a Strong Terahertz Field. <i>Physical Review Letters</i> , 2017, 119, 077403.	7.8	7
75	Decoupling the Two Roles of Ga Droplets in the Self-Catalyzed Growth of GaAs Nanowires on SiO ₂ /Si(111) Substrates. <i>Crystal Growth and Design</i> , 2017, 17, 5276-5282.	3.0	26
76	Ultrafast Processes in Graphene: From Fundamental Manybody Interactions to Device Applications. <i>Annalen Der Physik</i> , 2017, 529, 1700022.	2.4	10
77	Carrier Dynamics in Graphene: Ultrafast Many-Particle Phenomena. <i>Annalen Der Physik</i> , 2017, 529, 1700038.	2.4	26
78	Symmetry-Breaking Supercollisions in Landau-Quantized Graphene. <i>Physical Review Letters</i> , 2017, 119, 067405.	7.8	10
79	Low-temperature intracenter relaxation times of shallow donors in germanium. <i>JETP Letters</i> , 2017, 106, 571-575.	1.4	15
80	THz Nonlinear Response of Landau-Quantized Graphene. , 2017, , .		0
81	Long-lived Anisotropy of Photoexcited Graphene Electrons. , 2016, , .		0
82	Plasmonic efficiency enhancement at the anode of strip line photoconductive terahertz emitters. <i>Optics Express</i> , 2016, 24, 22628.	3.4	15
83	Inter-sublevel dynamics in single InAs/GaAs quantum dots induced by strong terahertz excitation. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	6
84	Excitonic mobility edge and ultra-short photoluminescence decay time in n-type GaAsN. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	2
85	Tracing the Gouy phase shift of focused, radially polarized THz pulses. , 2016, , .		0
86	First Terahertz-range Experiments on Pump-Probe Setup at Novosibirsk free Electron Laser. <i>Physics Procedia</i> , 2016, 84, 152-156.	1.2	12
87	Lattice vibrations and electrical transport in (Bi ₂) ₂ Se ₃ films. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	4
88	Electrode width dependent performance of THz photoconductive emitters. , 2016, , .		1
89	Role of Transient Reflection in Graphene Nonlinear Infrared Optics. <i>ACS Photonics</i> , 2016, 3, 1069-1075.	6.6	14
90	Dynamics of nonequilibrium electrons on neutral center states of interstitial magnesium donors in silicon. <i>Physical Review B</i> , 2016, 94, .	3.2	9

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91	Slow Noncollinear Coulomb Scattering in the Vicinity of the Dirac Point in Graphene. Physical Review Letters, 2016, 117, 087401.	7.8	40
92	High-Field High-Repetition-Rate Sources for the Coherent THz Control of Matter. Scientific Reports, 2016, 6, 22256.	3.3	121
93	Droplet-Confined Alternate Pulsed Epitaxy of GaAs Nanowires on Si Substrates down to CMOS-Compatible Temperatures. Nano Letters, 2016, 16, 4032-4039.	9.1	20
94	Gouy phase shift of a tightly focused, radially polarized beam. Optica, 2016, 3, 35.	9.3	32
95	Far-Infrared Nonlinear Optics in Multilayer Epitaxial Graphene. , 2016, , .		0
96	Terahertz pump " Terahertz probe system at Novosibirsk free electron laser: Commissioning and results of first experiments. , 2016, , .		0
97	Plasmonic Superlensing in Doped GaAs. Nano Letters, 2015, 15, 1057-1061.	9.1	48
98	Single-pulse picking at kHz repetition rates using a Ge plasma switch at the free-electron laser FELBE. Review of Scientific Instruments, 2015, 86, 063103.	1.3	8
99	Universal ultrafast detector for short optical pulses based on graphene. Optics Express, 2015, 23, 28728.	3.4	23
100	High-Temperature Photon-Noise-Limited Performance Terahertz Quantum-Well Photodetectors. IEEE Transactions on Terahertz Science and Technology, 2015, 5, 715-724.	3.1	12
101	Direct determination of the electron effective mass of GaAsN by terahertz cyclotron resonance spectroscopy. Applied Physics Letters, 2015, 107, .	3.3	9
102	Carrier dynamics in Landau-quantized graphene featuring strong Auger scattering. Nature Physics, 2015, 11, 75-81.	16.7	79
103	Two-photon quantum well infrared photodetectors below 6 THz. Infrared Physics and Technology, 2015, 70, 30-33.	2.9	12
104	Intraband carrier dynamics in Landau-quantized multilayer epitaxial graphene. New Journal of Physics, 2014, 16, 123021.	2.9	17
105	Characterizing intra-exciton Coulomb scattering in terahertz excitations. Applied Physics Letters, 2014, 105, 201109.	3.3	3
106	Observation and manipulation of dipole-forbidden exciton transitions in semiconductors. , 2014, , .		0
107	Magnetic control of Coulomb scattering and terahertz transitions among excitons. Physical Review B, 2014, 89, .	3.2	5
108	Systematic investigation of terahertz-induced excitonic Rabi splitting. Physical Review B, 2014, 89, .	3.2	16

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109	Near-room-temperature photon-noise-limited quantum well infrared photodetector. Laser and Photonics Reviews, 2014, 8, 297-302.	8.7	8
110	Re-Examining the Doping Effect on the Performance of Quantum Well Infrared Photodetectors. IEEE Journal of Quantum Electronics, 2014, 50, 3-6.	1.9	6
111	Dark current mechanism of terahertz quantum-well photodetectors. Journal of Applied Physics, 2014, 116, .	2.5	8
112	Anisotropy of Excitation and Relaxation of Photogenerated Charge Carriers in Graphene. Nano Letters, 2014, 14, 1504-1507.	9.1	77
113	Ultrafast graphene-based broadband THz detector. Applied Physics Letters, 2013, 103, .	3.3	174
114	Terahertz generation and detection with InGaAs-based large-area photoconductive devices excited at 1.55 μm . Applied Physics Letters, 2013, 103, .	3.3	18
115	InGaAs-based large area photoconductive emitters for 1.55 μm excitation. , 2013, , .		0
116	Longitudinal fields in focused terahertz beams. , 2013, , .		0
117	Large area photoconductive terahertz emitter for 1.55 μm excitation based on an InGaAs heterostructure. Nanotechnology, 2013, 24, 214007.	2.6	25
118	Semiconductor quantum well excitons in strong, narrowband terahertz fields. New Journal of Physics, 2013, 15, 065007.	2.9	29
119	Time-resolved spectroscopy on epitaxial graphene in the infrared spectral range: relaxation dynamics and saturation behavior. Journal of Physics Condensed Matter, 2013, 25, 054202.	1.8	59
120	The THz user facility FELBE at the radiation source ELBE of Helmholtz-Zentrum Dresden-Rossendorf. , 2013, , .		1
121	Extra-long hole spin relaxation time in InGaAs/GaAs quantum wells probed by cyclotron resonance spectroscopy. , 2013, , .		0
122	Inter-sublevel dephasing in quantum dots. , 2013, , .		0
123	Intersublevel dephasing in InAs/GaAs quantum dots below the Reststrahlen band. Applied Physics Letters, 2013, 103, .	3.3	4
124	THz free-electron laser spectroscopy of magnetoexcitons in semiconductor quantum wells. , 2013, , .		0
125	Observation of Forbidden Exciton Transitions Mediated by Coulomb Interactions in Photoexcited Semiconductor Quantum Wells. Physical Review Letters, 2013, 110, 137404.	7.8	27
126	Long spin relaxation time of holes in InGaAs/GaAs quantum wells probed by cyclotron resonance spectroscopy. Physical Review B, 2013, 87, .	3.2	1

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127	Plasmonic focusing on metal and semiconductor disks under radially polarized terahertz illumination. , 2013, , .		0
128	Ultrafast graphene-based THz detection at room temperature. , 2013, , .		0
129	Terahertz-induced effects on excitons in magnetic field. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1218-1221.	0.8	2
130	Universal phase relation between longitudinal and transverse fields observed in focused terahertz beams. New Journal of Physics, 2012, 14, 103049.	2.9	47
131	Fano effect due to ponderomotive coupling in intersubband response of semiconductor quantum wells. Physical Review B, 2012, 86, .	3.2	1
132	In-plane interdot carrier transfer in InAs/GaAs quantum dots. Applied Physics Letters, 2012, 100, 152101.	3.3	7
133	Master equation approach of classical noise in intersubband detectors. Physical Review B, 2012, 85, .	3.2	11
134	Free-electron laser spectroscopy of quantum well exciton dynamics. , 2012, , .		0
135	Study of lifetimes and photoconductivity relaxation in heterostructures with $\text{Hg}_x\text{Cd}_{1-x}\text{Te}/\text{Cd}_{1-y}\text{Hg}_y\text{Te}$ quantum wells. Semiconductors, 2012, 46, 1362-1366.	0.5	34
136	Intersublevel Spectroscopy on Single InAs-Quantum Dots by Terahertz Near-Field Microscopy. Nano Letters, 2012, 12, 4336-4340.	9.1	51
137	Nonlinear transmission dynamics in graphene close to the Dirac point. , 2011, , .		0
138	Mid-infrared pump-related electric-field domains in GaAs/(Al,Ga)As quantum-cascade structures for terahertz lasing without population inversion. Journal of Applied Physics, 2011, 110, 103104.	2.5	12
139	Direct Evidence Of Long Lived Trapped Carriers In InGaAs/GaAs Quantum Dots Studied Using Terahertz-activated Luminescence Measurements. , 2011, , .		0
140	Terahertz Induced Intra-excitonic Autler-Townes Effect In Semiconductor Quantum Wells. AIP Conference Proceedings, 2011, , .	0.4	0
141	Photoluminescence dynamics in GaAs/AlGaAs quantum wells under pulsed intersubband excitation. Applied Physics Letters, 2011, 99, .	3.3	16
142	Carrier Relaxation in Epitaxial Graphene Photoexcited Near the Dirac Point. Physical Review Letters, 2011, 107, 237401.	7.8	269
143	Terahertz nonlinear optics using intra-excitonic quantum well transitions: Sideband generation and AC Stark splitting. Physica Status Solidi (B): Basic Research, 2011, 248, 859-862.	1.5	9
144	Modification to the central-cell correction of germanium acceptors. Physical Review B, 2011, 84, .	3.2	3

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145	Simultaneous time and wavelength resolved spectroscopy under two-colour near infrared and terahertz excitation. Review of Scientific Instruments, 2011, 82, 103107.	1.3	23
146	Compact magnetospectrometer for pulsed magnets based on infrared quantum cascade lasers. Review of Scientific Instruments, 2011, 82, 033108.	1.3	15
147	Ultrafast carrier capture and THz resonances in InGaAs quantum posts. Proceedings of SPIE, 2011, , .	0.8	0
148	Time resolved spectroscopy on quantum dots and graphene at the FELBE free-electron laser. Proceedings of SPIE, 2011, , .	0.8	0
149	The cyclotron resonance of holes in InGaAs/GaAs heterostructures with quantum wells in quantizing magnetic fields. Semiconductors, 2010, 44, 1492-1494.	0.5	7
150	Longitudinal fields in focused radially polarized terahertz beams. , 2010, , .		0
151	Infrared magneto-spectroscopy using quantum cascade lasers. , 2010, , .		0
152	Terahertz activated luminescence of trapped carriers in InGaAs/GaAs quantum dots. Applied Physics Letters, 2010, 97, 031101.	3.3	9
153	Terahertz optical sideband emission in self-assembled quantum dots. Applied Physics Letters, 2010, 96, .	3.3	3
154	Intraexciton terahertz nonlinear optics in semiconductor quantum wells: Sideband generation and AC Stark splitting. , 2010, , .		0
155	Excitation wavelength dependence of phase matched terahertz emission from a GaAs slab. Optics Express, 2010, 18, 19574.	3.4	2
156	Quantitative determination of the charge carrier concentration of ion implanted silicon by IR-near-field spectroscopy. Optics Express, 2010, 18, 26206.	3.4	23
157	Observation of the Intraexciton Autler-Townes Effect in AlGaAs Semiconductor Quantum Wells. Physical Review Letters. 2010. 105. 167401.	7.8	113
158	Carrier Capture Studies in InGaAs Quantum Posts. , 2010, , .		0
159	Mode-locking via active gain modulation in quantum cascade lasers. , 2009, , .		1
160	High-field splitting of the cyclotron resonance absorption in strained InGaAs wells. Physical Review B, 2009, 79, .	3.2	19
161	Ultrafast carrier capture in InGaAs quantum posts. Applied Physics Letters, 2009, 95, .	3.3	10
162	Resonant enhancement of second order sideband generation for intraexcitonic transitions in GaAs/AlGaAs multiple quantum wells. Applied Physics Letters, 2009, 94, 241105.	3.3	22

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163	Fano Signatures in the Intersubband Terahertz Response of Optically Excited Semiconductor Quantum Wells. <i>Physical Review Letters</i> , 2009, 102, 127403.	7.8	27
164	Free-space propagation of radially and azimuthally polarized terahertz Bessel-Gauss beams. , 2009, , .		0
165	Large-area terahertz emitters based on GaInAsN. , 2009, , .		0
166	Terahertz emitters and detectors for radially and azimuthally polarized beams. <i>Proceedings of SPIE</i> , 2009, , .	0.8	0
167	Quadratic detection with two-photon quantum well infrared photodetectors. <i>Infrared Physics and Technology</i> , 2009, 52, 419-423.	2.9	7
168	Terahertz Bessel-Gauss beams of radial and azimuthal polarization from microstructured photoconductive antennas. <i>Optics Express</i> , 2009, 17, 1571.	3.4	68
169	Terahertz two-photon quantum well infrared photodetector. <i>Optics Express</i> , 2009, 17, 12279.	3.4	24
170	Mode-locked pulses from mid-infrared Quantum Cascade Lasers. <i>Optics Express</i> , 2009, 17, 12929.	3.4	168
171	Two color pump-probe studies of intraminiband relaxation in doped GaAs/AlGaAs superlattices. , 2009, , .		0
172	Fano profile in the intersubband terahertz response of photoexcited GaAs/AlGaAs quantum wells. <i>Journal of Physics: Conference Series</i> , 2009, 193, 012073.	0.4	1
173	Inefficiency of intervalley transfer in narrow InGaAs/AlAsSb quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 229-231.	0.8	5
174	Generation and Detection of THz Radiation With Scalable Antennas Based on GaAs Substrates With Different Carrier Lifetimes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2008, 14, 449-457.	2.9	41
175	Multimode regimes in quantum cascade lasers: From coherent instabilities to spatial hole burning. <i>Physical Review A</i> , 2008, 77, .	2.5	184
176	Two-photon photocurrent autocorrelation using intersubband transitions at nearly-resonant excitation. <i>Optics Express</i> , 2008, 16, 1523.	3.4	7
177	Leistungsstarke Emittter und einfach handhabbare Detektoren für die Terahertz-Time-Domain-Spektroskopie (Powerful Emitters and Easy-to-Use Detectors for Terahertz Time-Domain Spectroscopy) Tj ETQq1 1 0.784314 rgB0, Overlock 10 Tf 50		
178	Science at the Dresden High Magnetic Field Laboratory. <i>AIP Conference Proceedings</i> , 2008, , .	0.4	9
179	Terahertz emission from a large-area GaInAsN emitter. <i>Applied Physics Letters</i> , 2008, 93, 101102.	3.3	9
180	Terahertz vector beams. , 2008, , .		0

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181	Two-color pump-probe studies of intraminiband relaxation in doped GaAs ⁺ /AlGaAs superlattices. Applied Physics Letters, 2008, 92, 051104.	3.3	2
182	Room-temperature midinfrared two-photon photodetector. Applied Physics Letters, 2008, 93, .	3.3	13
183	Easy-to-Use Scalable Antennas for Coherent Detection of THz Radiation. Springer Proceedings in Physics, 2008, , 167-169.	0.2	0
184	Large-area photoconductive terahertz detectors. , 2007, , .		0
185	Two-photon photocurrent spectroscopy of electron intersubband relaxation and dephasing in quantum wells. Applied Physics Letters, 2007, 91, .	3.3	16
186	Coherent terahertz detection with a large-area photoconductive antenna. Applied Physics Letters, 2007, 91, .	3.3	36
187	Measurements of non-Gaussian noise in quantum wells. Physical Review B, 2007, 76, .	3.2	6
188	Non-Gaussian noise in quantum wells. , 2007, , .		0
189	Autocorrelation measurements of the FELBE free-electron laser and photocurrent saturation study in two-photon QWIPs. , 2007, , .		0
190	Portable THz cyclotron resonance spectrometer in the range 3 to 30THz. , 2007, , .		0
191	Impact of Interface Formation on Intersubband Transitions in MBE GaInAs:Si/AlAsSb Multiple Coupled DQWs. Indium Phosphide and Related Materials Conference (IPRM), IEEE International Conference on, 2007, , .	0.0	0
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193	Intersubband Relaxation Dynamics in Narrow InGaAs/AlAsSb Quantum Well Structures Studied by Femtosecond Pump-Probe Spectroscopy. AIP Conference Proceedings, 2007, , .	0.4	0
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